



# FP211

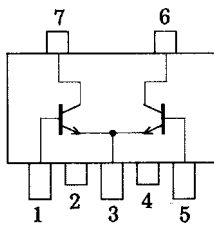
## NPN Epitaxial Planar Silicon Transistor

### Driver Applications

#### Features

- Composite type with 2 transistors (NPN) contained in one package, facilitating high-density mounting.
- The FP211 is formed with 2 chips being equivalent to the 2SD1623, placed in one package.

#### Electrical Connection



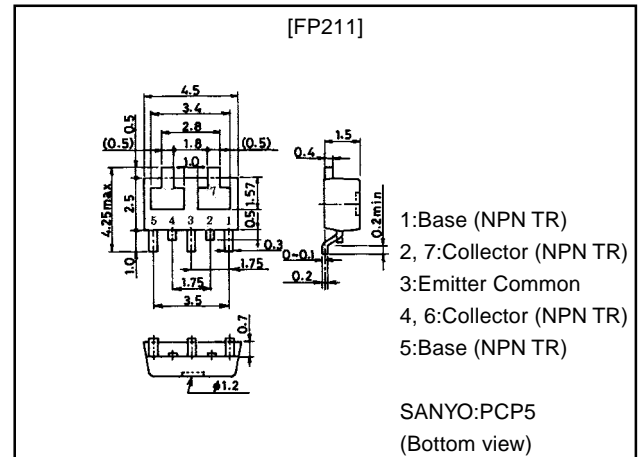
- 1:Base (NPN TR)  
 2, 7:Collector (NPN TR)  
 3:Emitter Common  
 4, 6:Collector (NPN TR)  
 5:Base (NPN TR)

(Top view)

#### Package Dimensions

unit:mm

2097A



#### Specifications

##### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CB0}$		60	V
Collector-to-Emitter Voltage	$V_{CEO}$		50	V
Emitter-to-Base Voltage	$V_{EBO}$		6	V
Collector Current	$I_C$		2	A
Collector Current (Pulse)	$I_{CP}$		4	A
Base Current	$I_B$		400	mA
Collector Dissipation	$P_C$	Mounted on ceramic board (250mm <sup>2</sup> ×0.8mm) 1 unit	0.8	W
Total Dissipation	$P_T$	Mounted on ceramic board (250mm <sup>2</sup> ×0.8mm)	1.1	W
Junction Temperature	$T_j$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

##### Electrical Characteristics at Ta=25°C

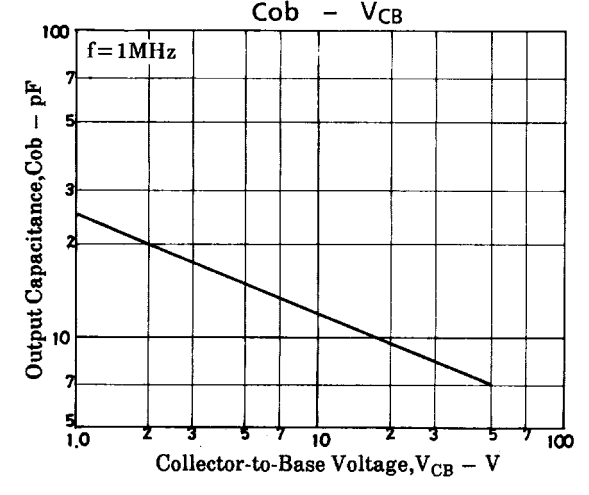
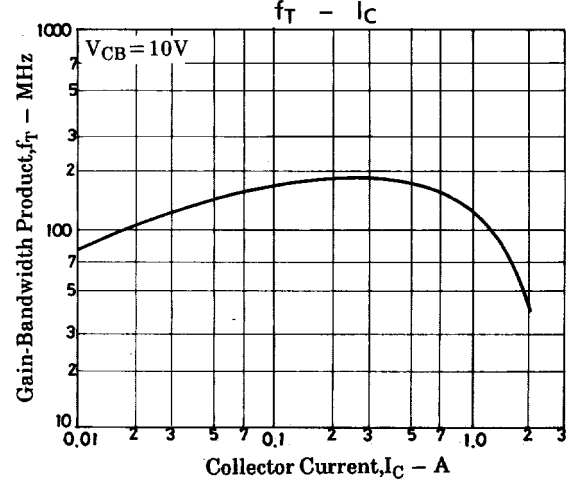
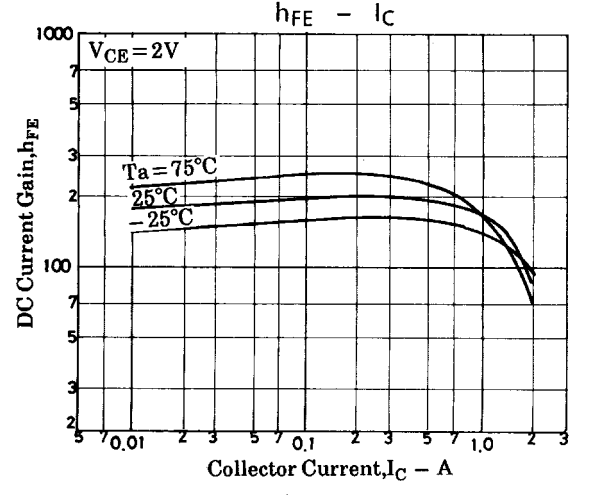
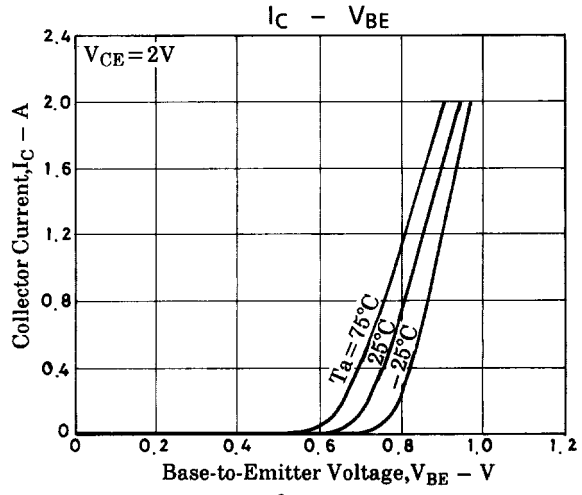
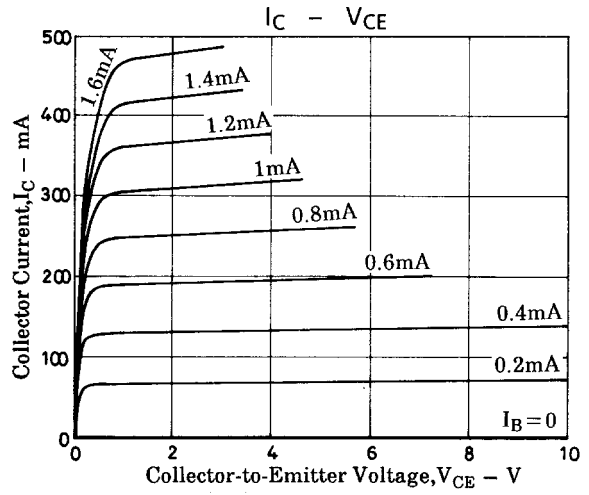
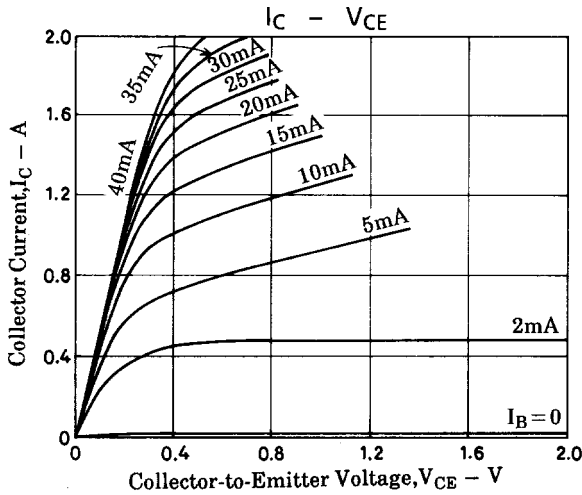
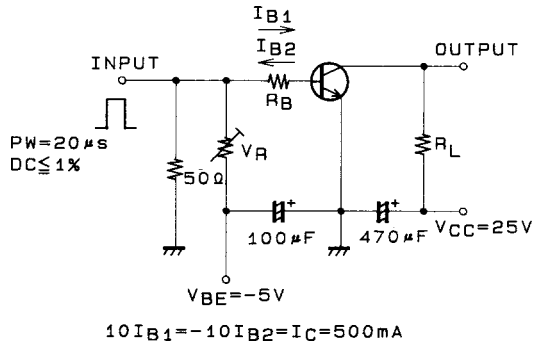
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=50V, I_E=0$			100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4V, I_C=0$			100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=2V, I_C=100mA$	140		400	
Gain-Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=50mA$		150		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1MHz$		12		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=50mA$		0.15	0.4	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=50mA$		0.9	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Turn-ON Time	$t_{on}$	See specified Test Circuit		60		ns
Storage Time	$t_{stg}$	See specified Test Circuit		550		ns
Fall Time	$t_f$	See specified Test Circuit		30		ns

Marking:211

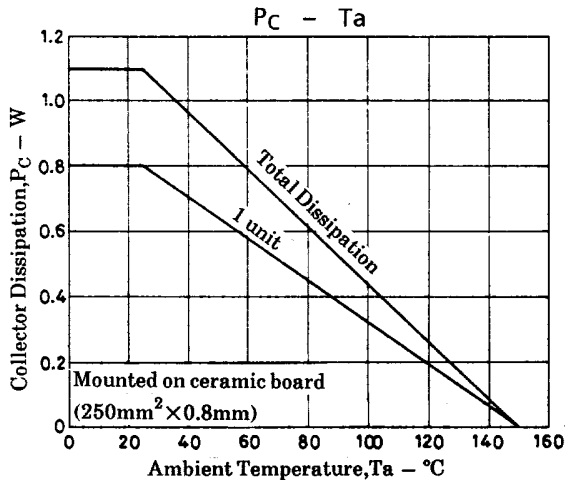
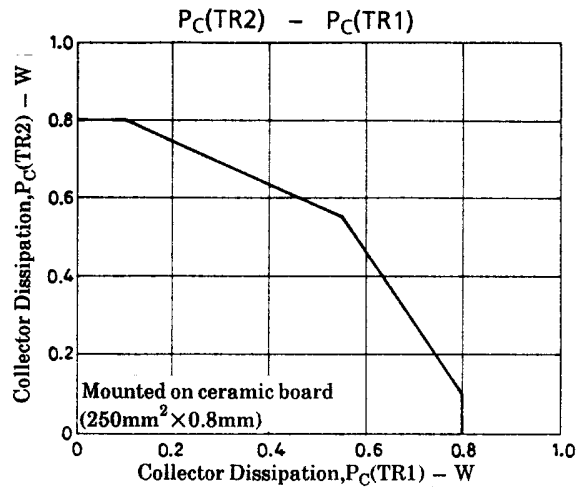
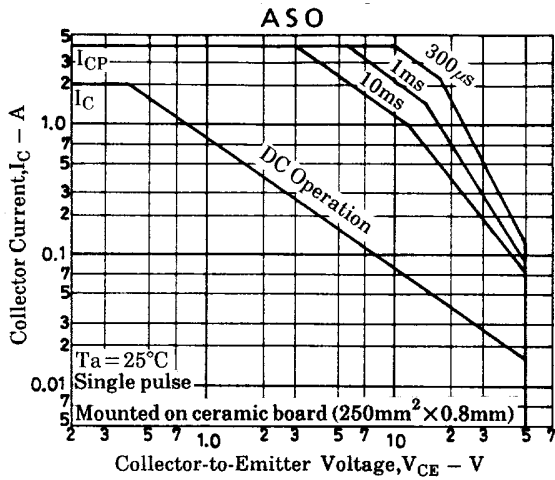
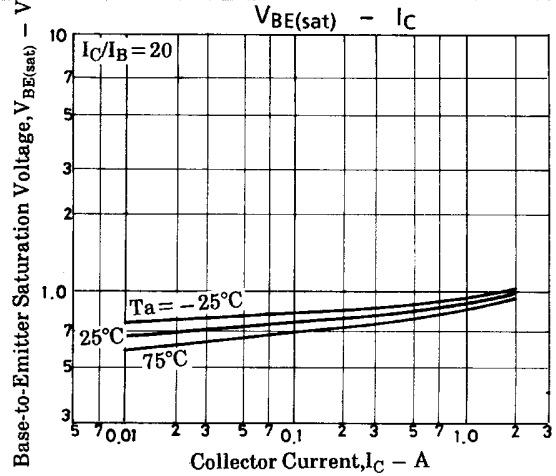
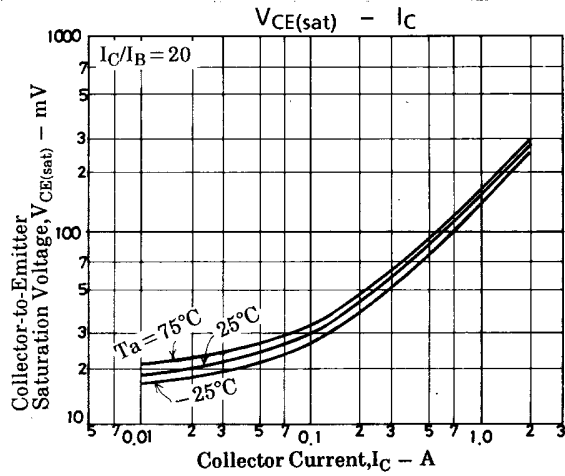
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Switching Time Test Circuit



# FP211



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